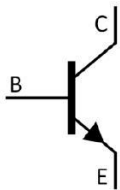


Silicon NPN transistor in a SOT-89 Plastic Package.

High h_{FE} and V_{CEO} , complementary pair with 2SA812T.

Audio frequency general amplifier application.

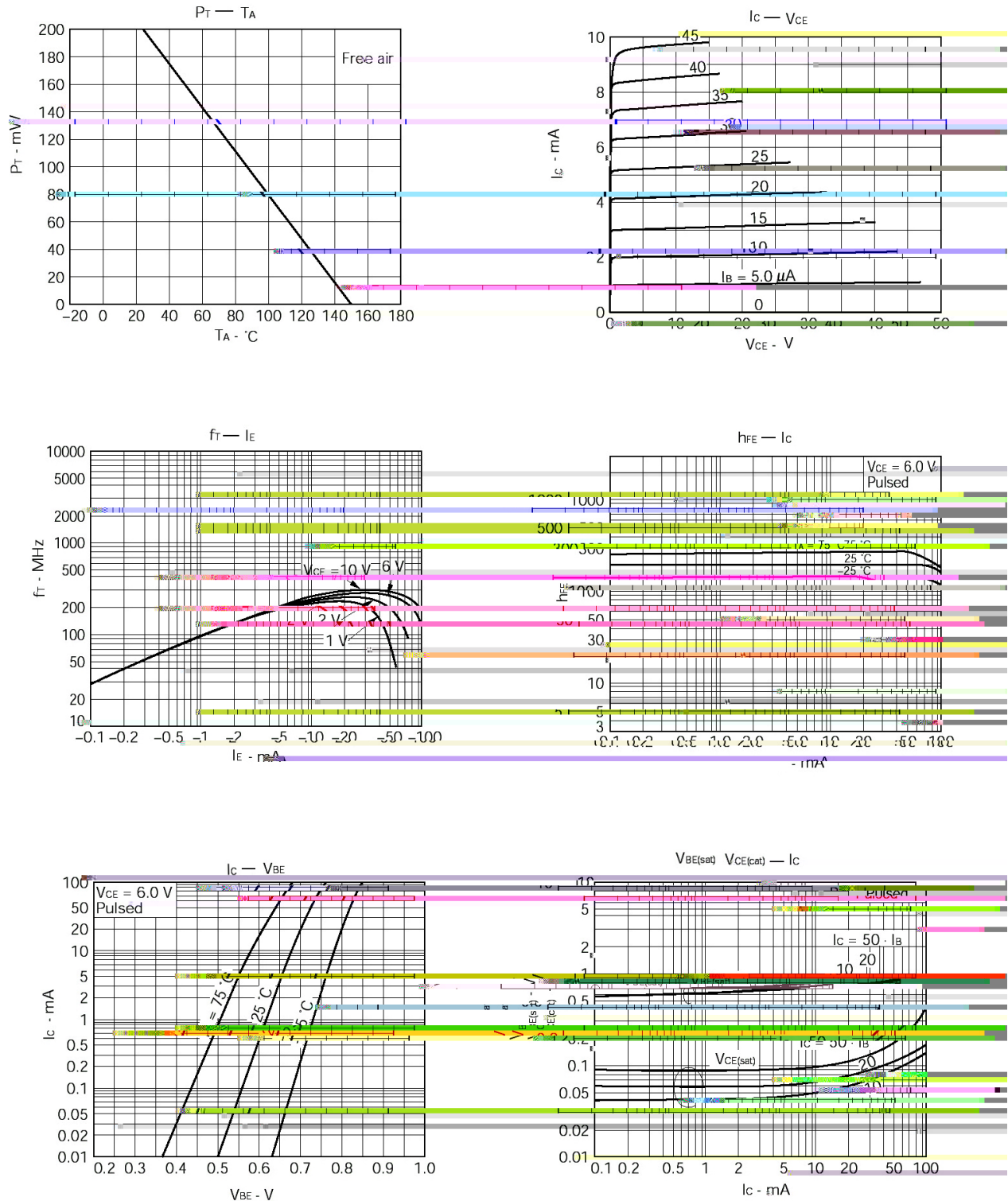


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	O	Y	G	L
h_{FE} Range	90 180	135 270	200 400	300 600
Marking	HL4	HL5	HL6	HL7

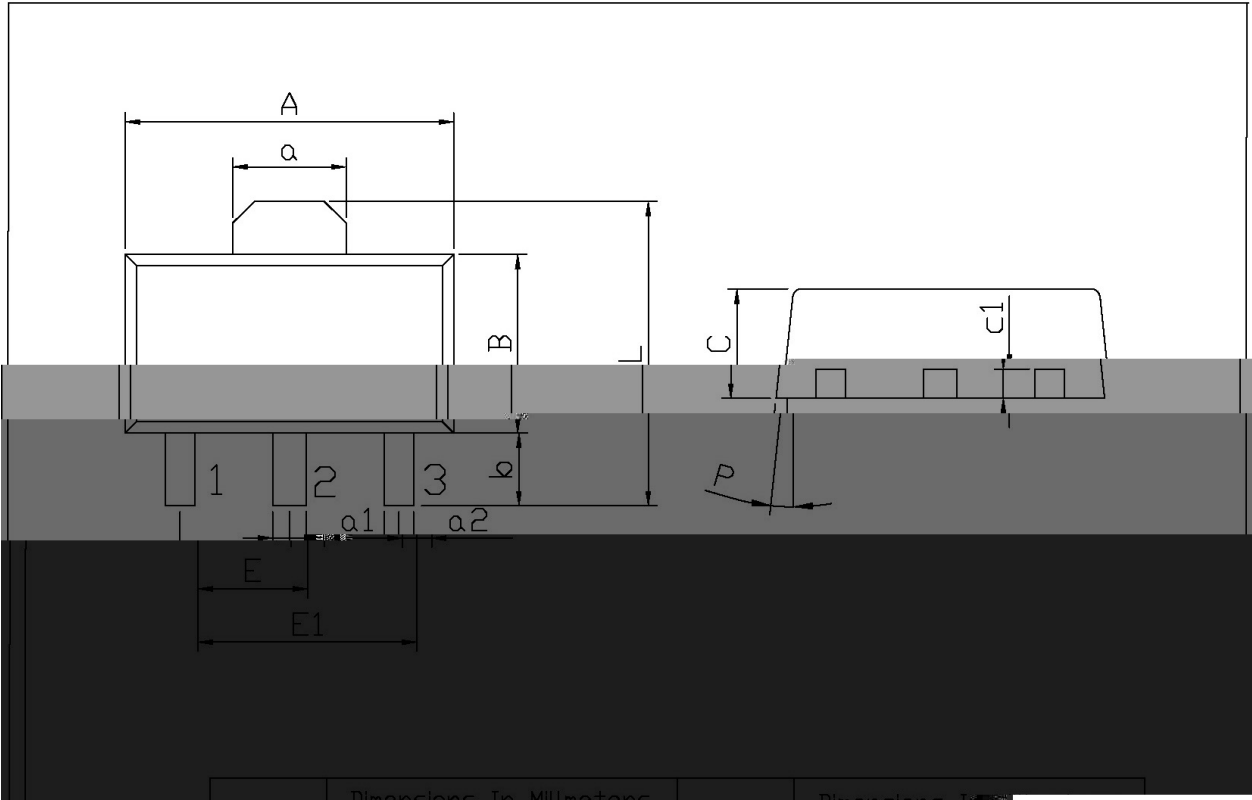
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous	I_C	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	90	200	600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.15	0.3	V
Emitter to Base Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.86	1.0	V
Emitter to Base Voltage	V_{BE}	$V_{CE}=6.0V$ $I_C=1.0mA$	0.55	0.62	0.65	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_C=10mA$		250		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $I_E=0$ $f=1.0MHz$		3.0		pF

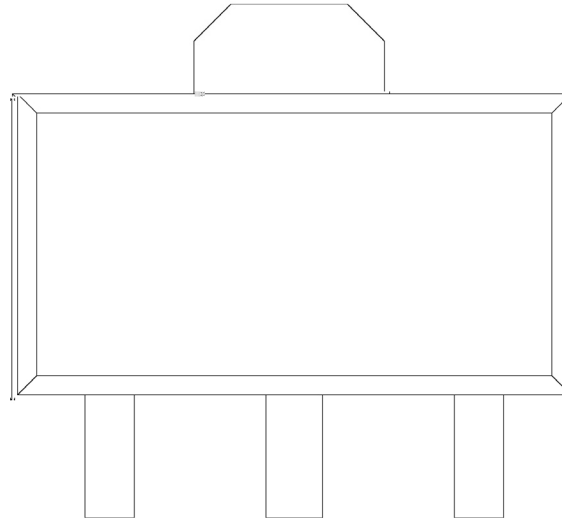


SOT-89

单位: mm



	3.80	4.40	4.70	0.30	0.30
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
E1	2.80	3.20			
b	0.80	1.20			



H

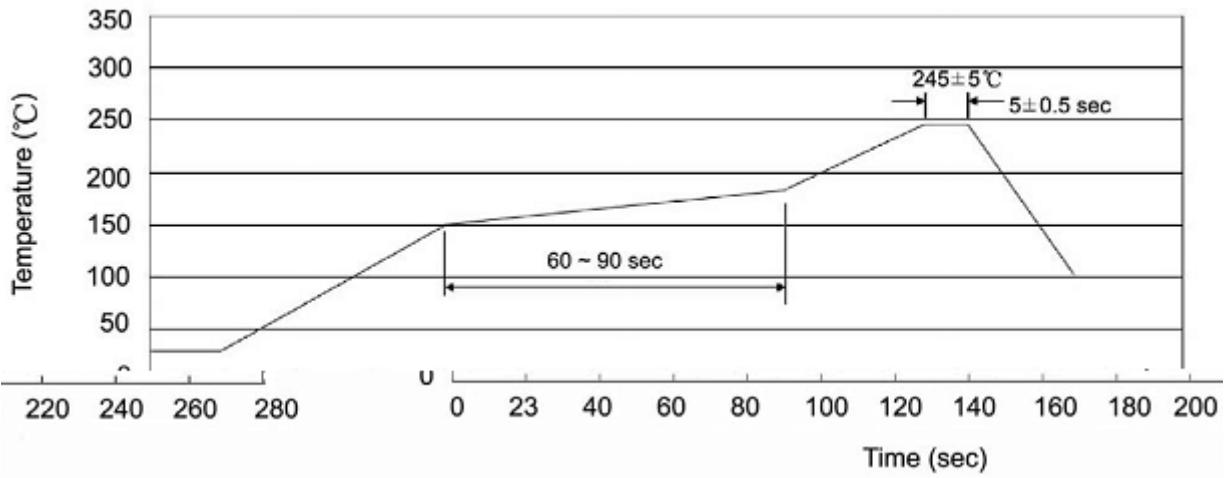
L5

Note:

H: Company Code.

L5: Product Type.

** : Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱